

Approaching the NA of Water: Immersion Lithography at 193nm

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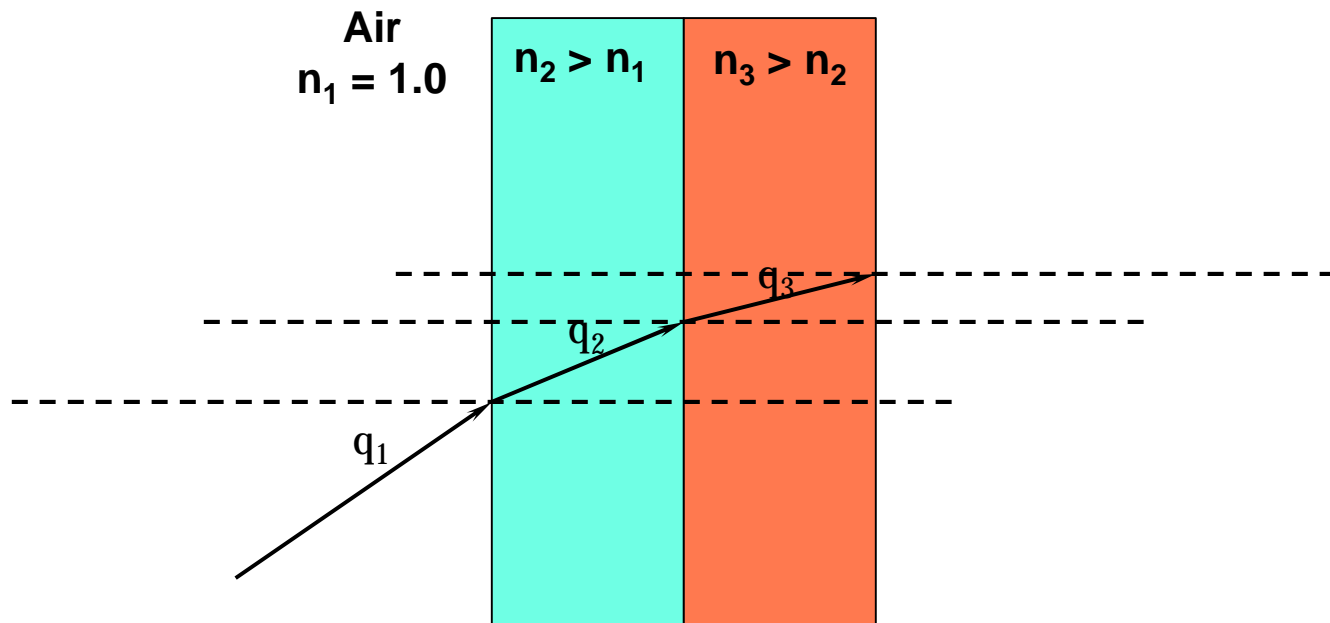


Outline

- 193nm immersion lithography to 38nm p/2
- Interferometric vs. projection lithography
- 1.05NA projection microstepper
- Homogeneous immersion and increasing refractive index

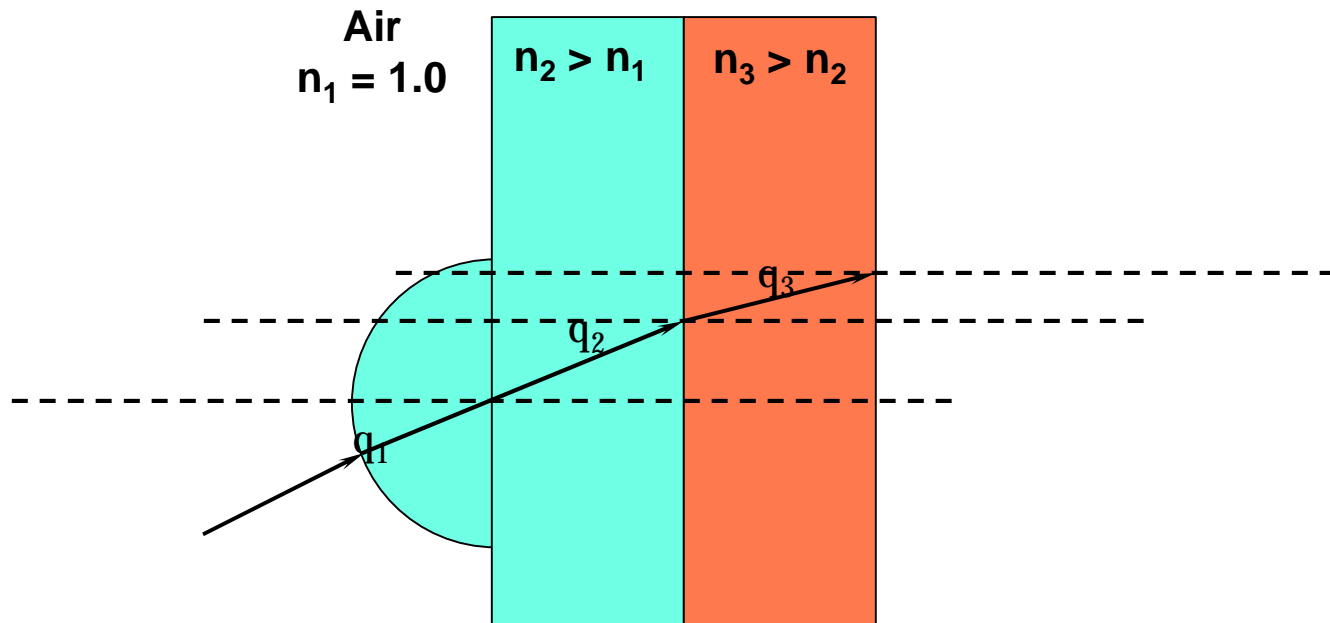


Increasing NA with Immersion



$$NA = n_1 \sin (q_1) = n_2 \sin (q_2) = n_3 \sin (q_3)$$

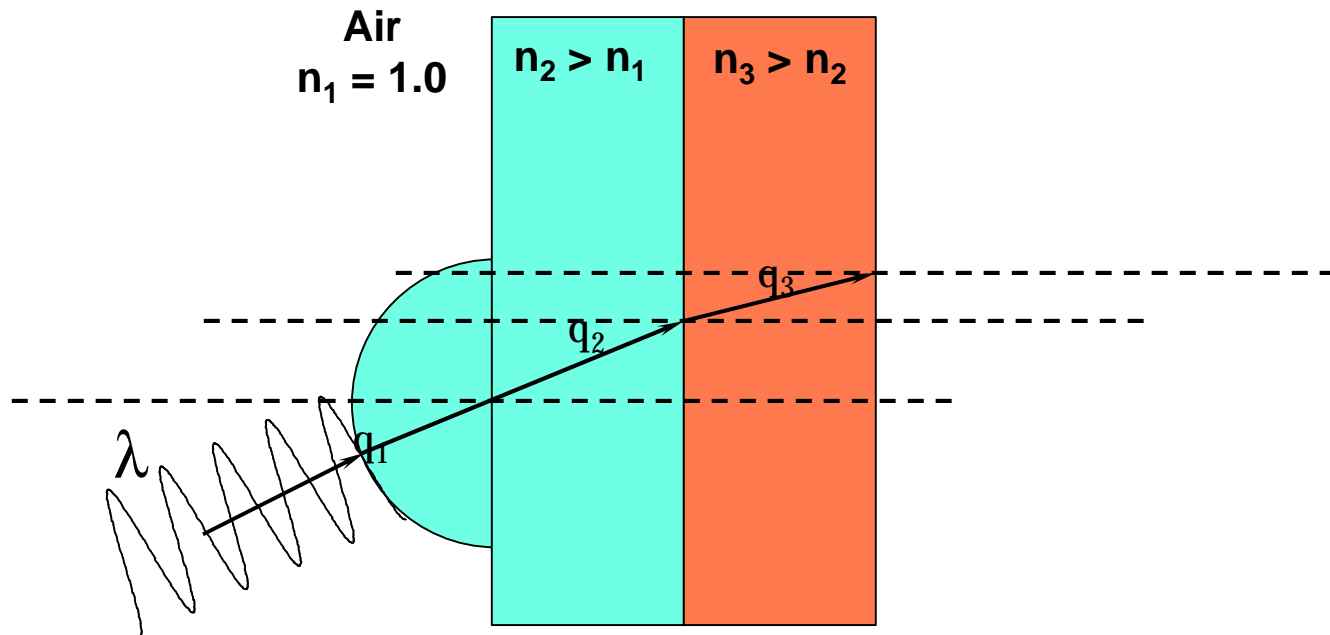
Increasing NA with Immersion



$$NA = n_1 \sin (q_1) = n_2 \sin (q_2) = n_3 \sin (q_3)$$

Increasing NA with Immersion

193nm or 134nm



Scaling of NA or wavelength?

ArF Immersion Talbot Lithography Breadboard “Half-ball” system

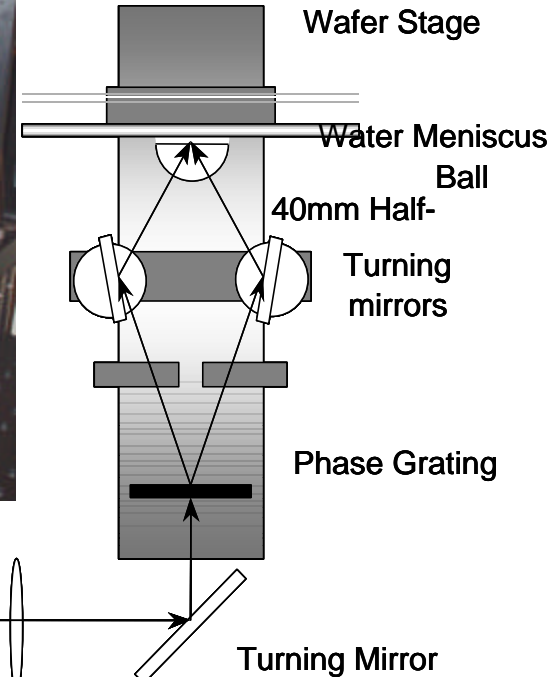
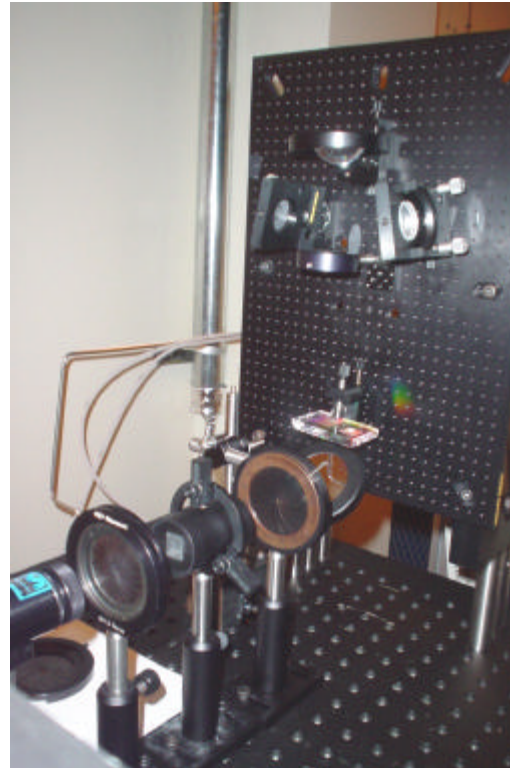
**+/- 1 Order Talbot
interferometer preserves
spatial coherence**

**Unstable excimer
resonator for 0.5mm
coherence length**

**Beam expansion increases
length to 2mm (field size)**

**Dual etalons provide 6pm
FWHM**

**Half ball interface allows
NA to 1.35**



Modified ArF laser
for temporal and
spatial coherence

Polarizer

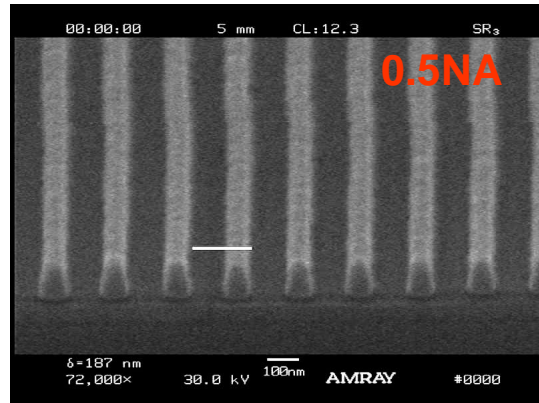
Shutter

Beam
Expander

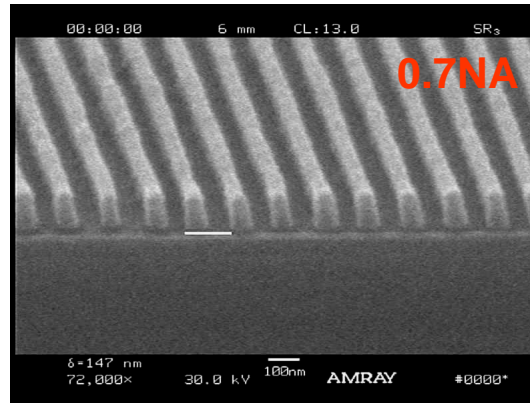
Turning Mirror

193i Resist Images 55-80nm Resolution

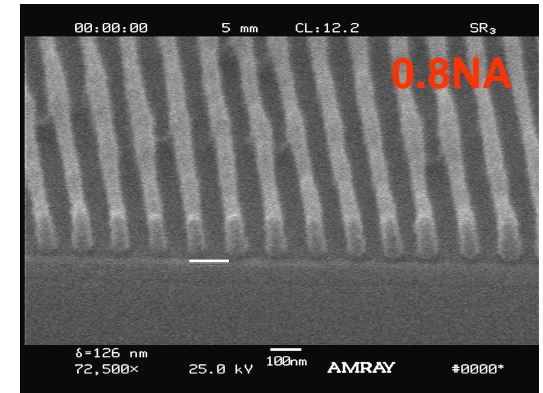
Shipley XP1020 over AR, 50-100nm film thickness, TOK topcoat, TE polarization



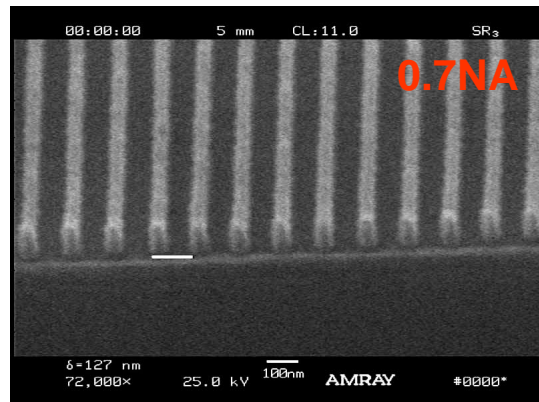
80nm 1:1.5



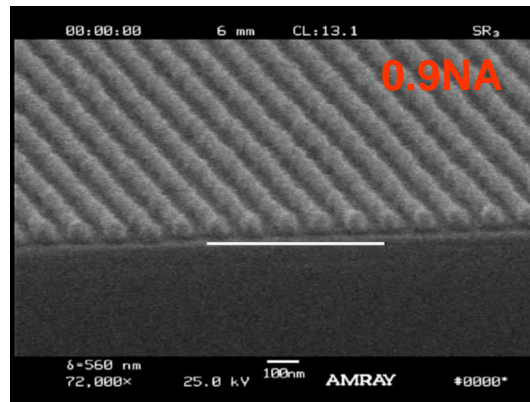
65nm 1:1



60nm 1:1



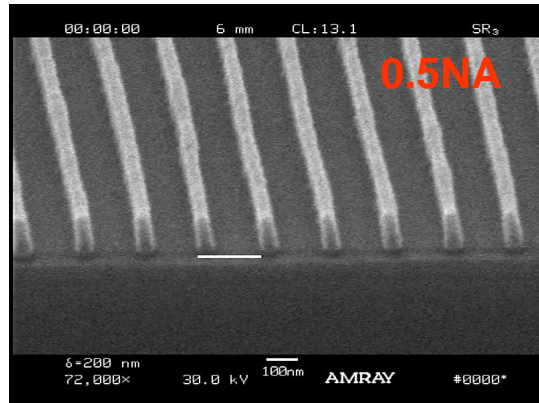
55nm 1:1.5



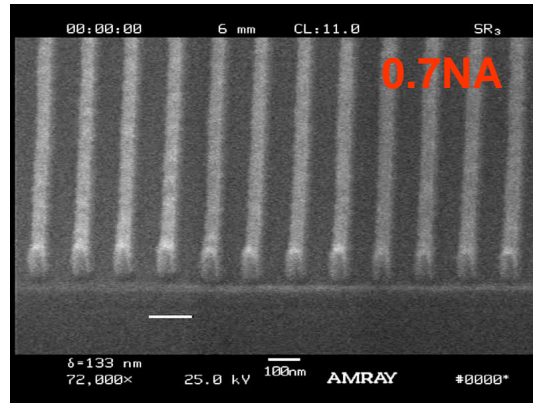
55nm 1:1

193i Resist Images 45-50nm Resolution

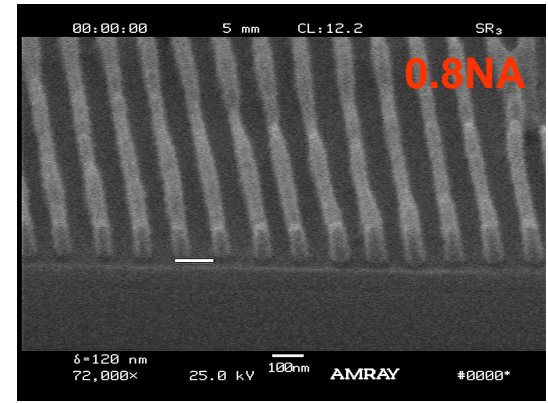
Shipley XP1020 over AR, 50-100nm film thickness, TOK topcoat, TE polarization



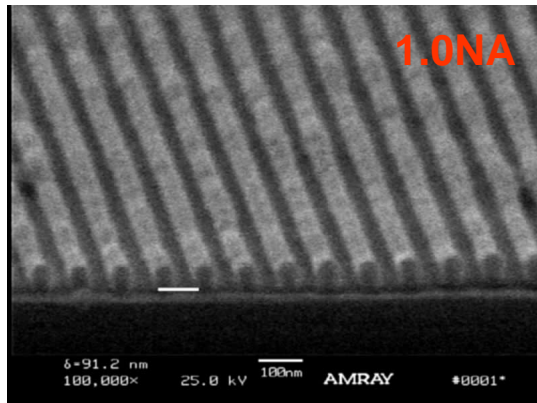
50nm 1:3



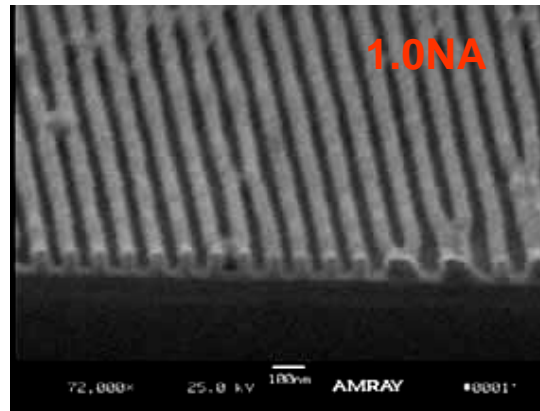
45nm 1:2



45nm 1:1.5



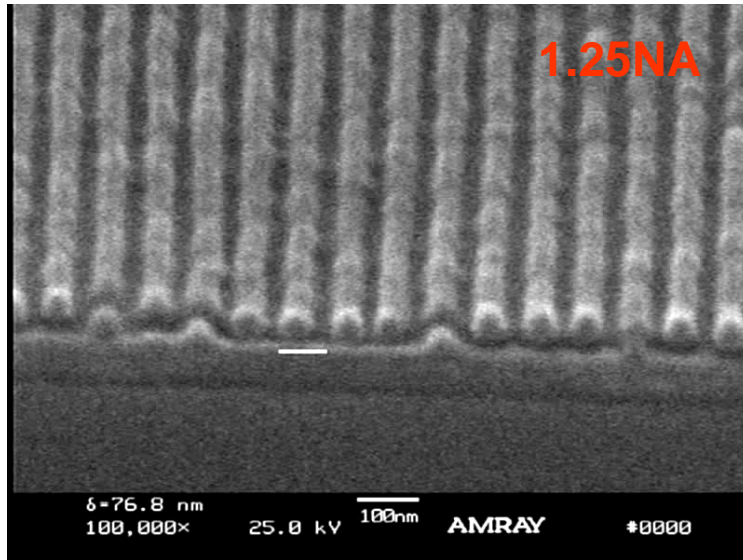
45nm 1:1 70nm
Shipley XP1020



45nm 1:1 80nm
TOK ILP012

193i Resist Images 38nm Resolution

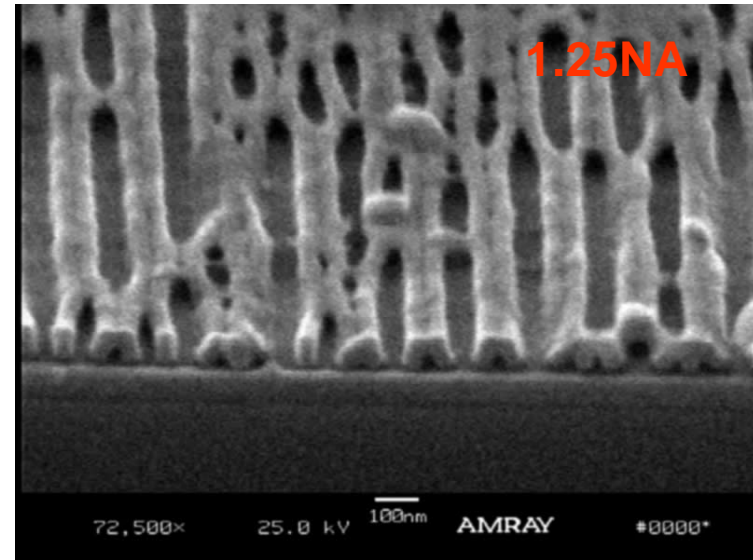
1.25NA Interference Lens, TE polarization



38nm p/2

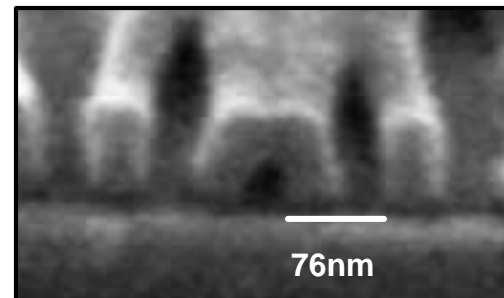
50nm XP1020

Early results show good optical contrast and resist potential



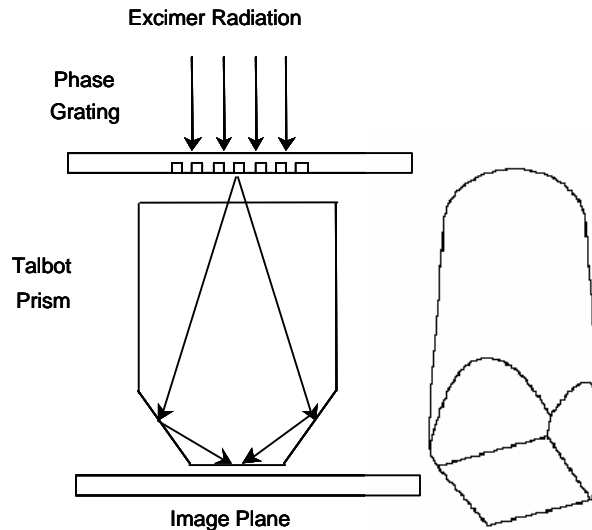
38nm 1:1

70nm XP1020



Compact Talbot Lens

Entire 193nm Talbot system incorporated into compact lens
600nm phase grating produces $\pm 1^{\text{st}}$ diffraction orders at 18.8°
Talbot lens angle increases NA up to 1.35
Line/space and contact patterns are possible
2/4 beam interference allow for large tolerances
Combined with beam expander and MgF_2 polarizer

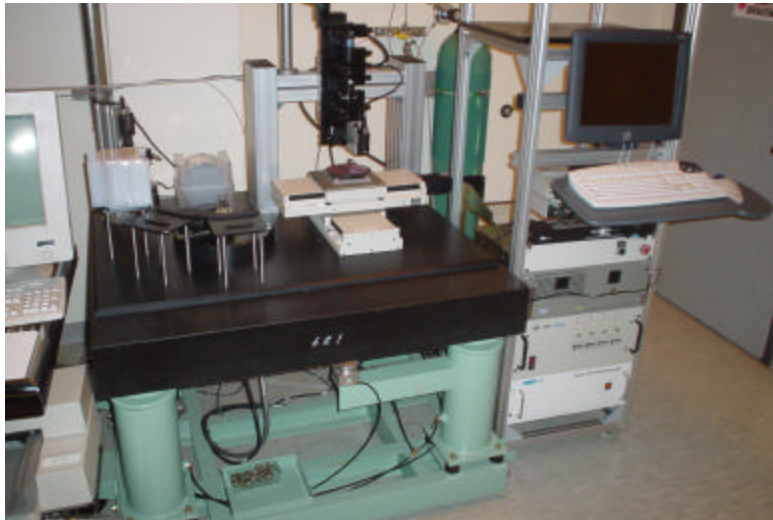


193 Prism Lens Designs
NA **half-pitch**

0.8	60nm
1.05	45nm
1.20	40nm
1.35	36nm

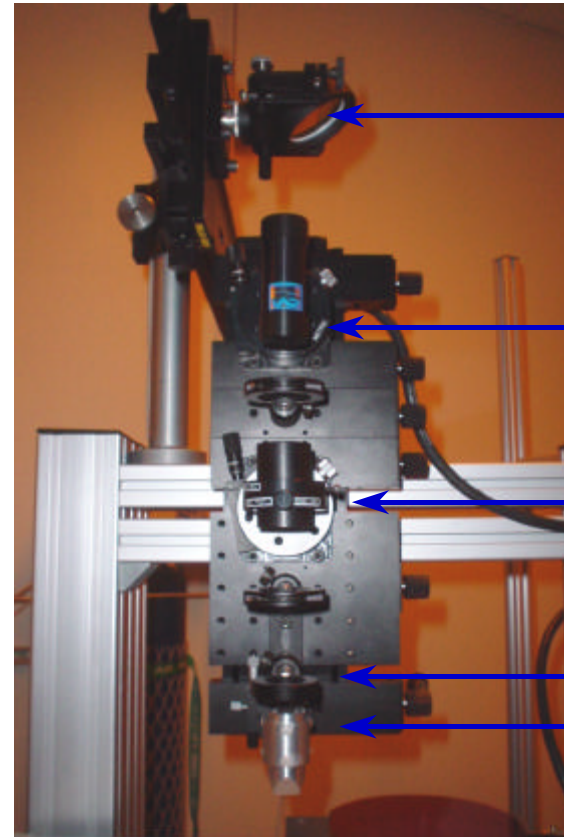
Talbot Immersion Research Tool

Workstation



- Linear guide bearing stage
- 200mm X-Y stage travel
- 6-8" robotic wafer handling
- Compact GAM ArF excimer
 - 5 mJ pulse energy
 - 6pm linewidth (FWHM)
 - 200 Hz rep. rate

Optical Column



Beam from ArF laser

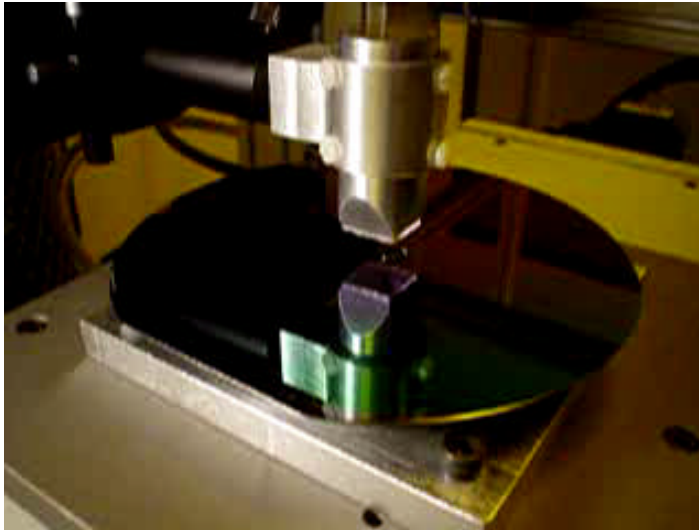
5X 193nm fused silica beam expander

193nm MgF2 Rochon polarizer

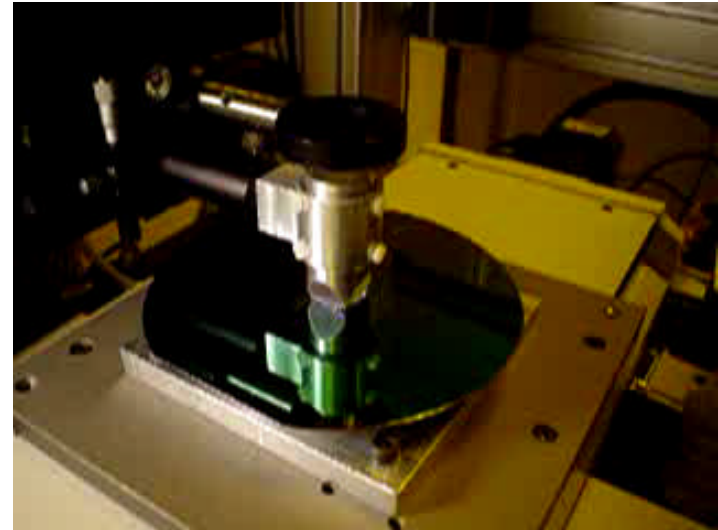
Phase shift mask (600nm 3.1 – 4.2X)

Smith-Talbot prism (1.0NA – 1.35NA)

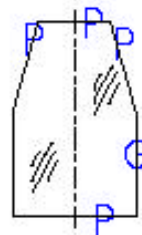
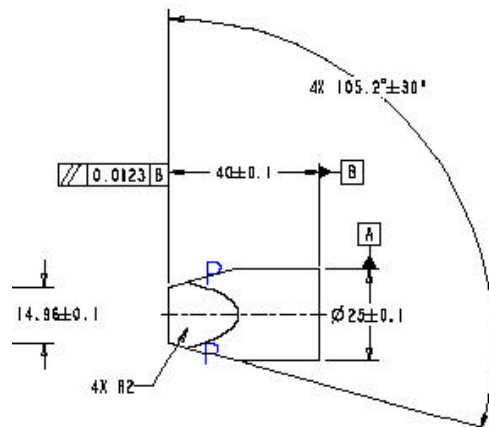
Water Handling at the Wafer Plane



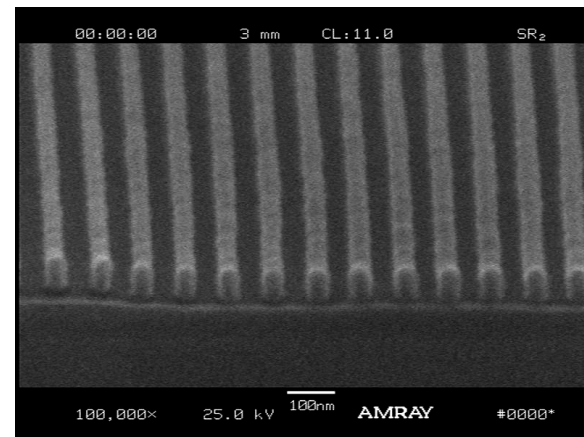
Contact with water



Stepping with water



45nm p/2 at 1.05NA



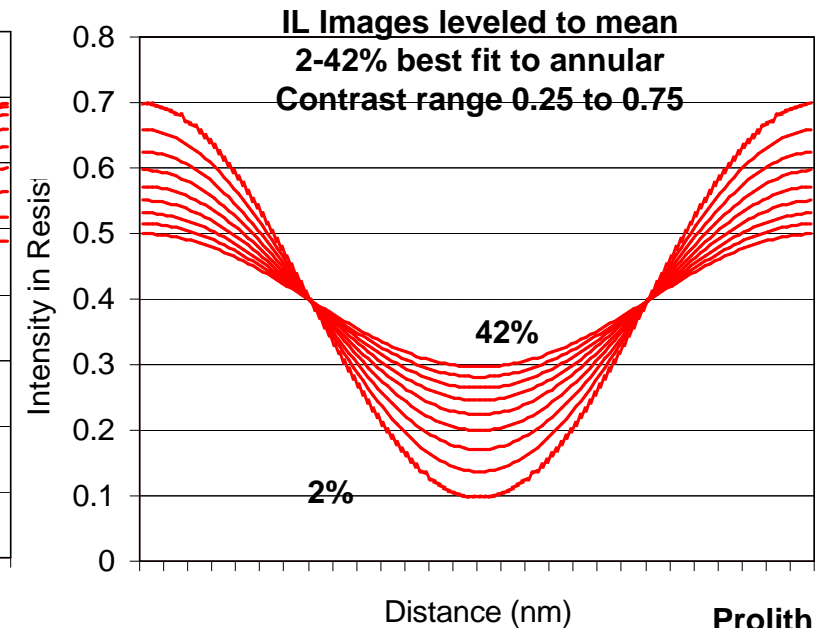
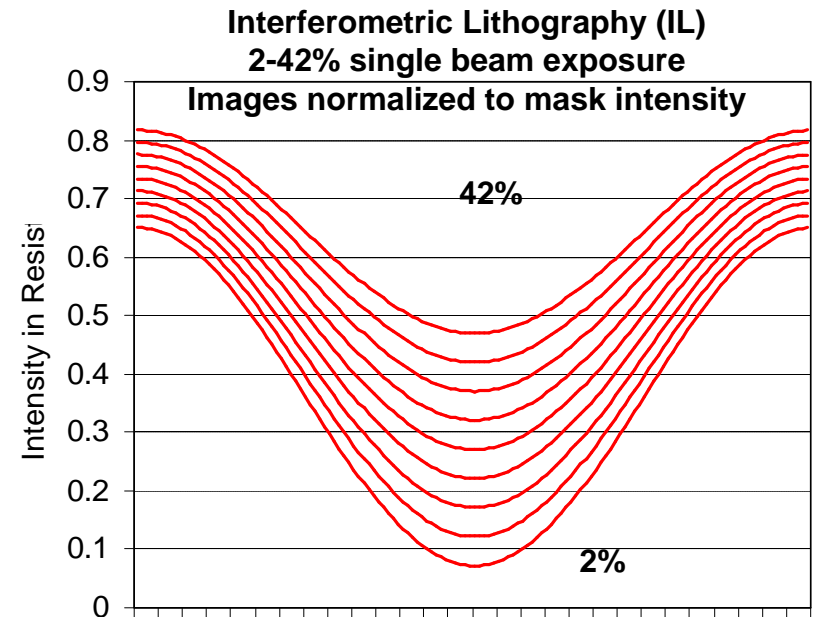
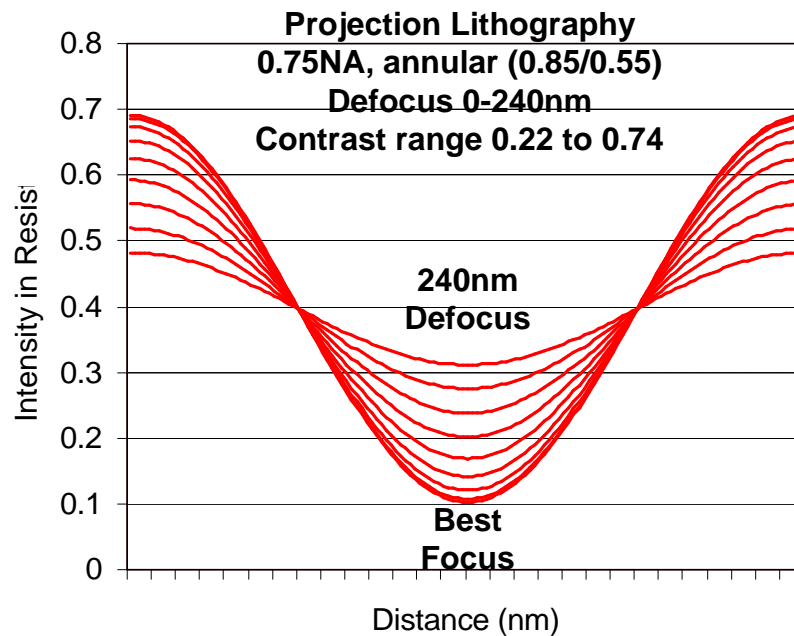
Interferometric Immersion vs. Projection Immersion Lithography

**How well can 2-beam interference
lithography predict projection
lithography?**



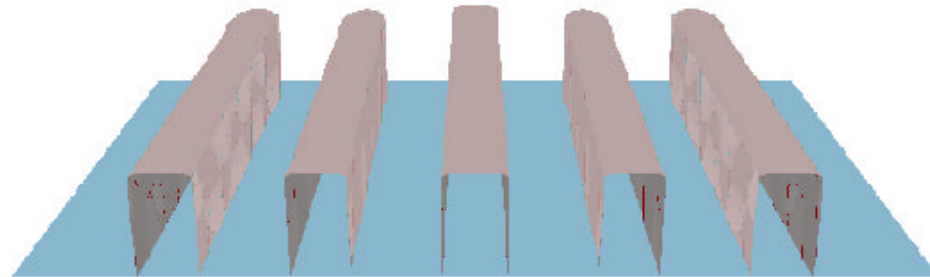
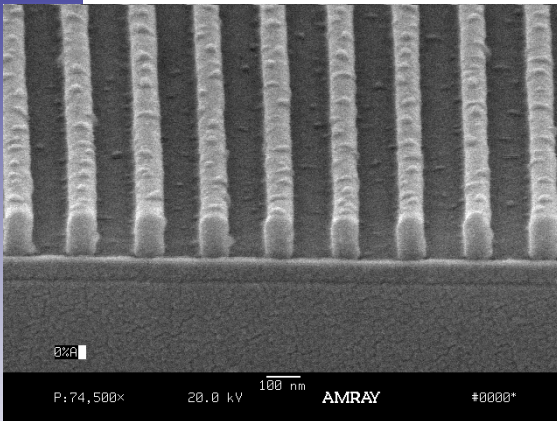
Resist Image Intensity Comparisons

**Projection vs. Interferometric
Lithography of 100nm 1:1 lines**
Resist index = 1.7, $a=0$
Vector Simulation



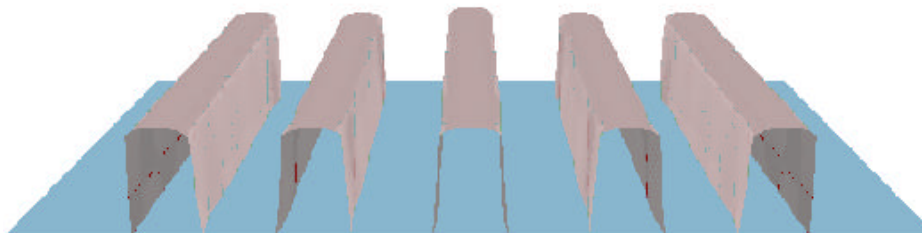
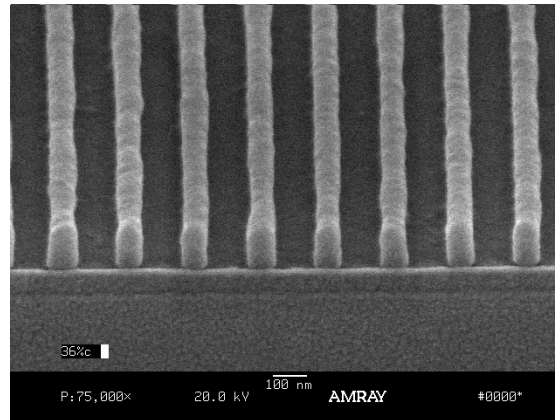
Immersion IL Images with demodulation

Full modulation
(Best Focus)



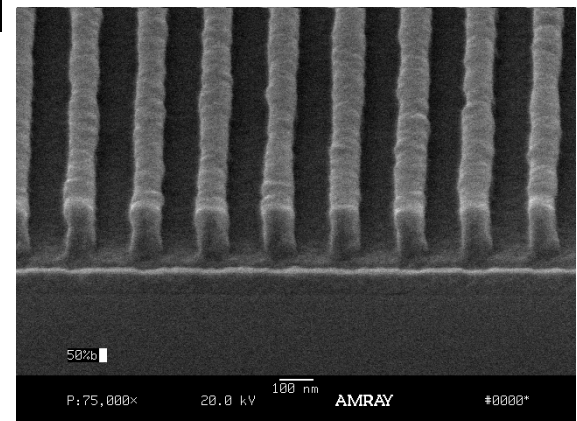
LPM simulation

30% demodulation
(150nm defocus)



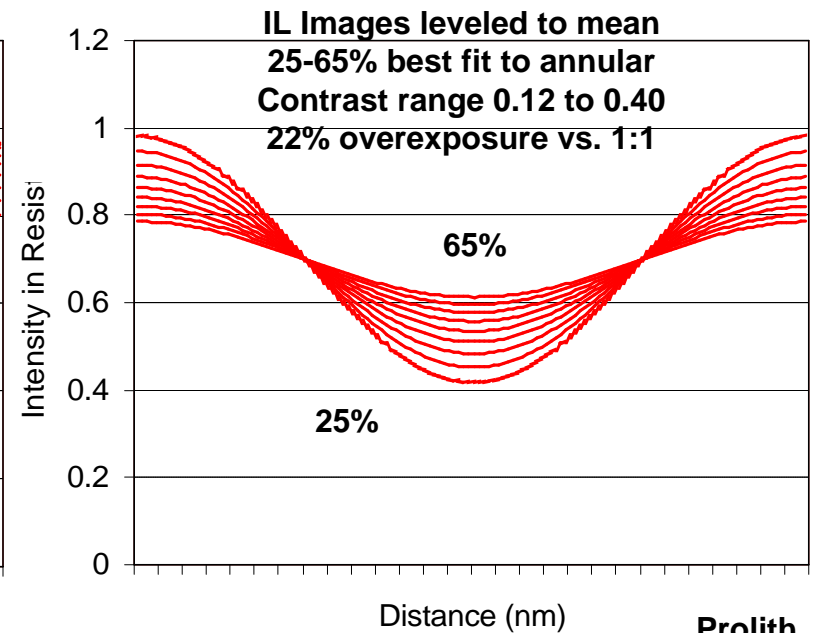
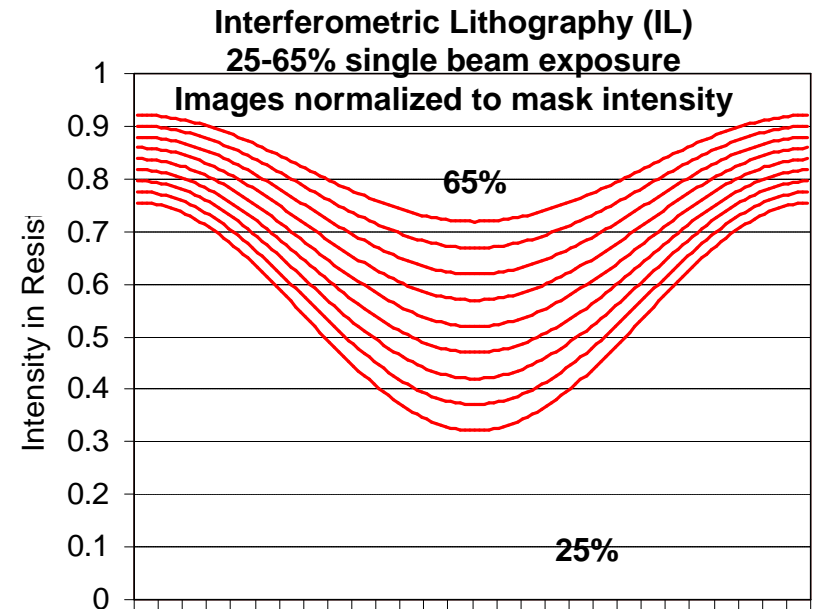
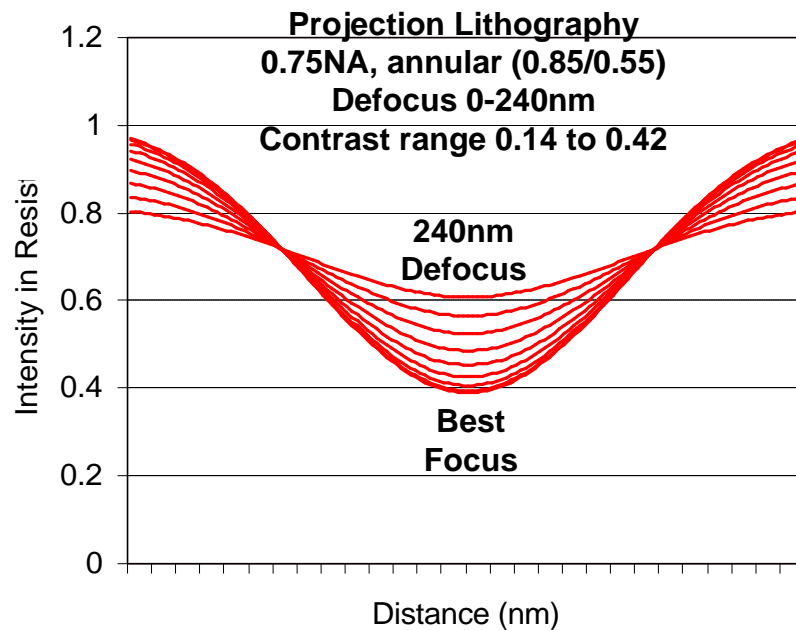
LPM simulation

50% demodulation
(220nm defocus)



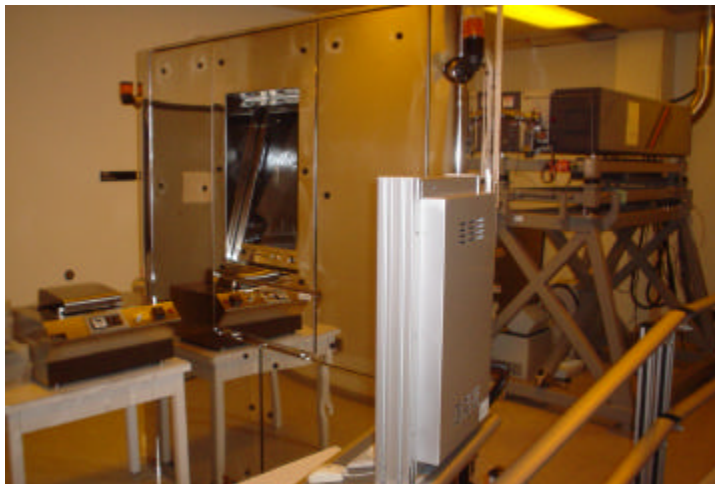
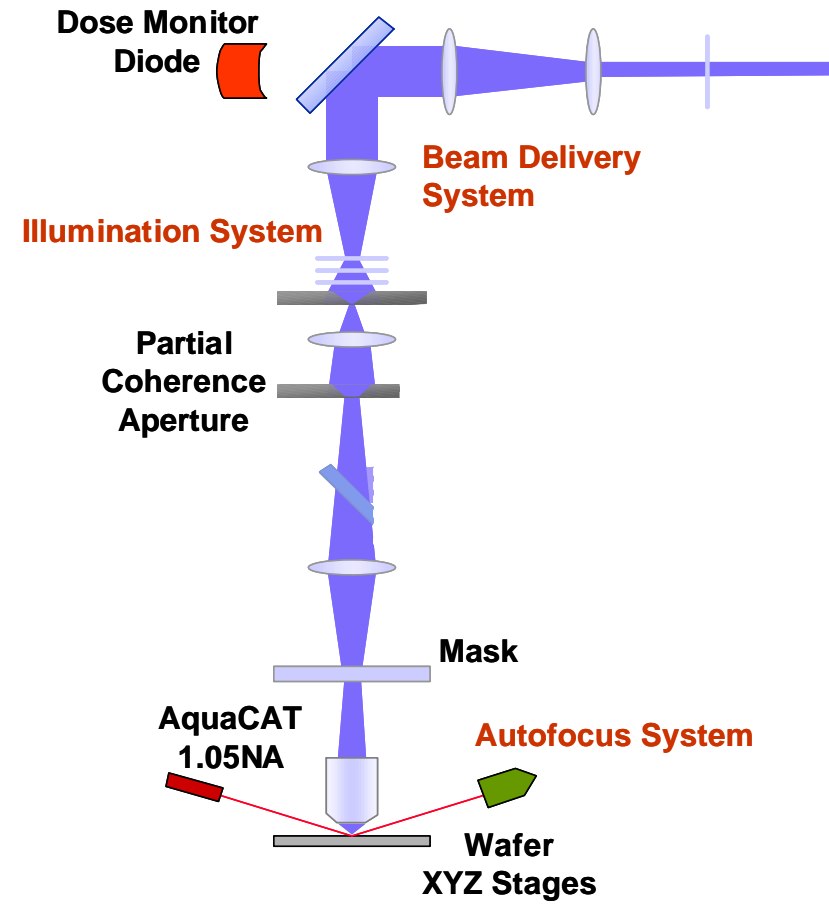
Resist Image Intensity Comparisons

**Projection vs. Interferometric
Lithography of 100nm 1:3 lines**
Resist index = 1.7, $a=0$
Vector Simulation

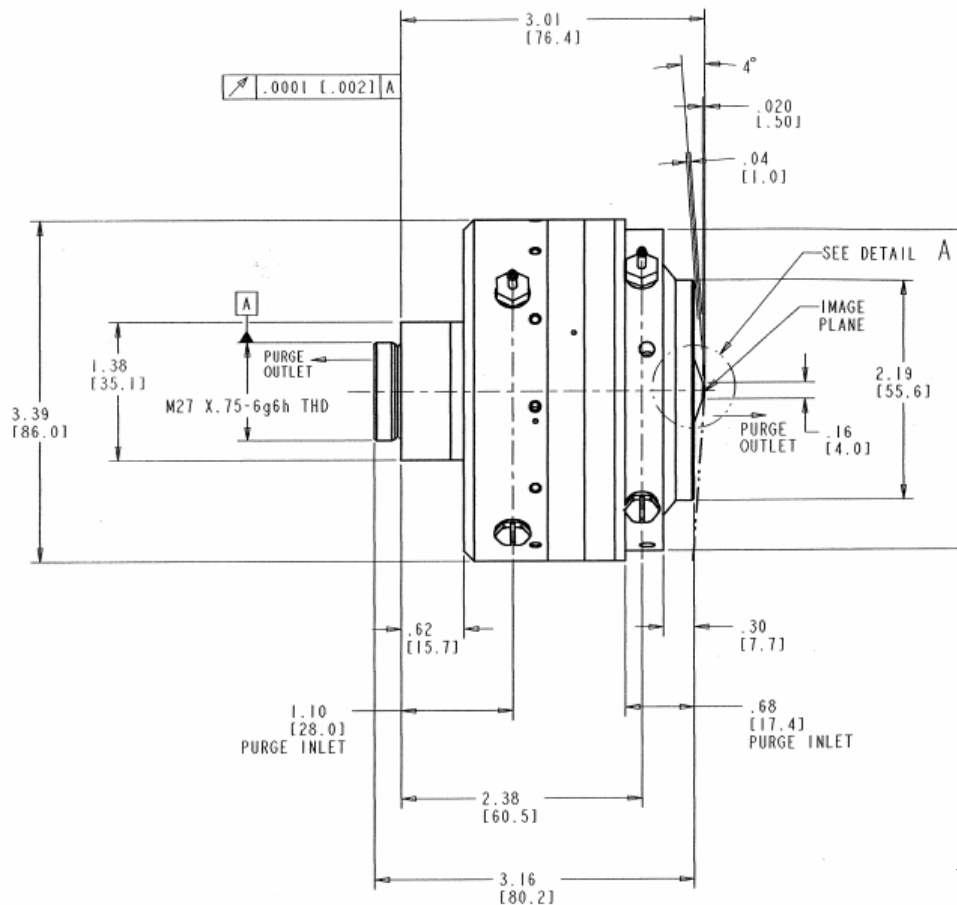


193nm Immersion MicroStepper

Exitech PS3000 / 1.05NA Corning Tropel AquaCAT

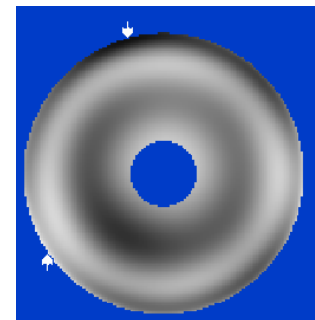
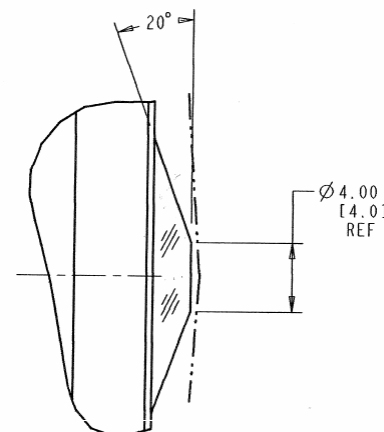


AquaCAT 193i Catadioptric Lens

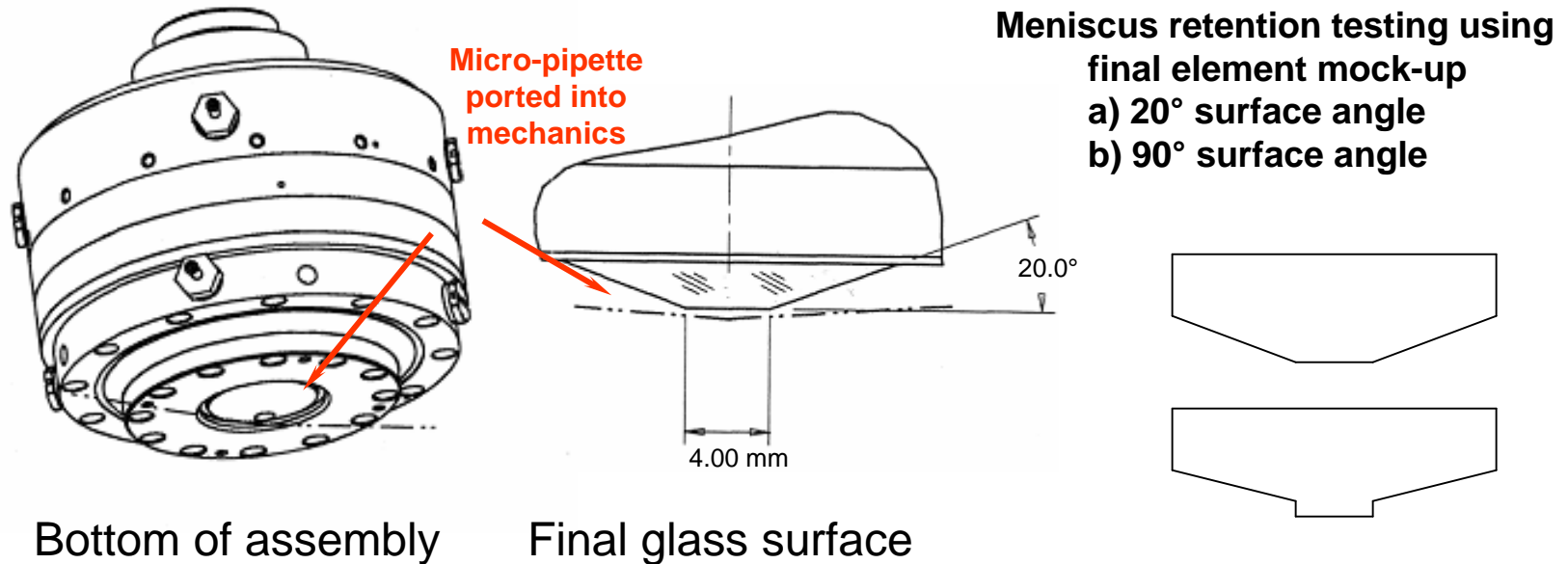


Lens Specifications

NA	1.05
Reduction	90X
Image field	0.1 mm
Wavelength	193.3 nm
Bandwidth	700 pm
Track length	210 mm +/- 10 mm
Entrance Pupil distance	210 mm +/- 10 mm
Material	SiO ₂
Immersion fluid	H ₂ O
Working distance	>0.5 mm
# of elements	8
% Obscuration	<15%
Measured wavefront	<0.05 waves rms (SPIE 5377-74)



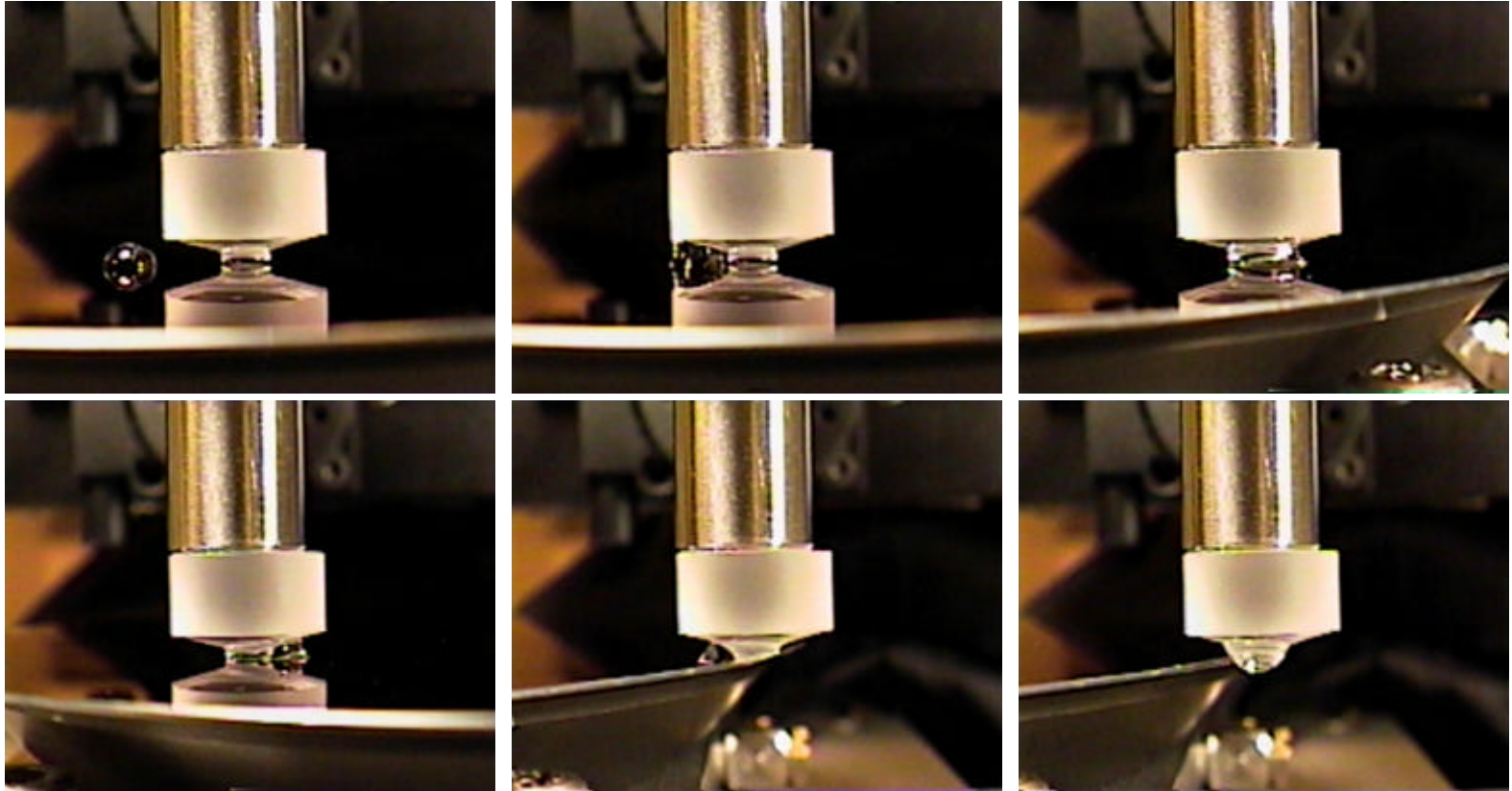
Fluid Injection and Meniscus



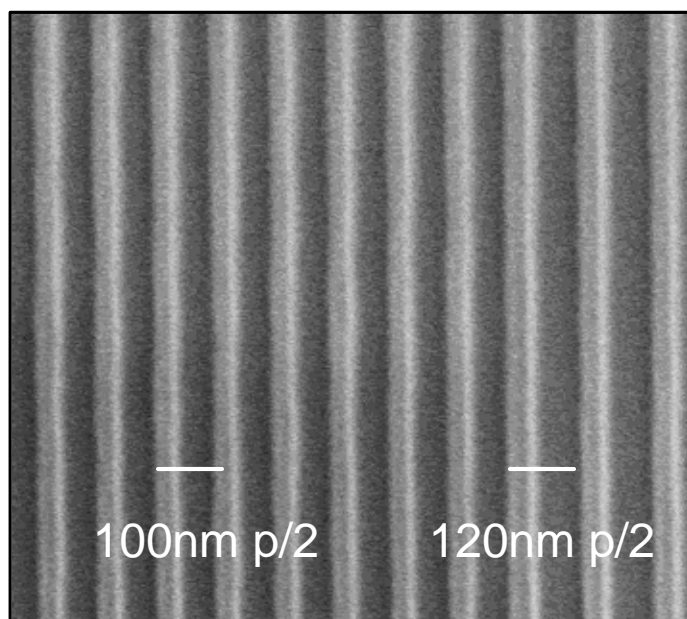
Water Introduction Considerations

1. Method – micro syringe pipette ~0.01 ml immersion volume in 3.5 sec using 10ml/hr Baxter APII syringe pump
2. Retention – surface tensioning to hold meniscus

Water Meniscus Retention Experimental Test Approach



Early Image Results



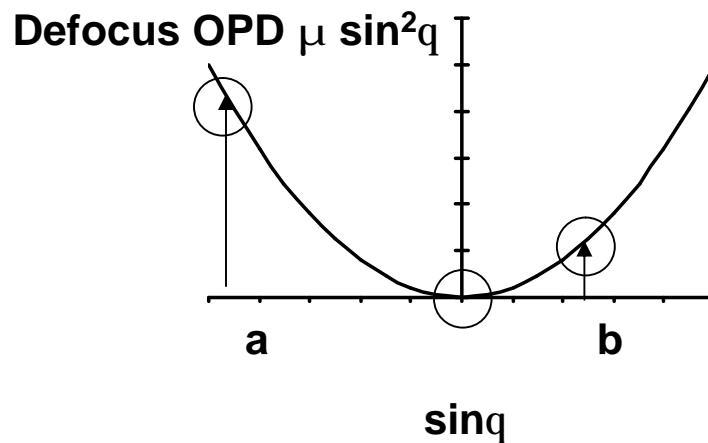
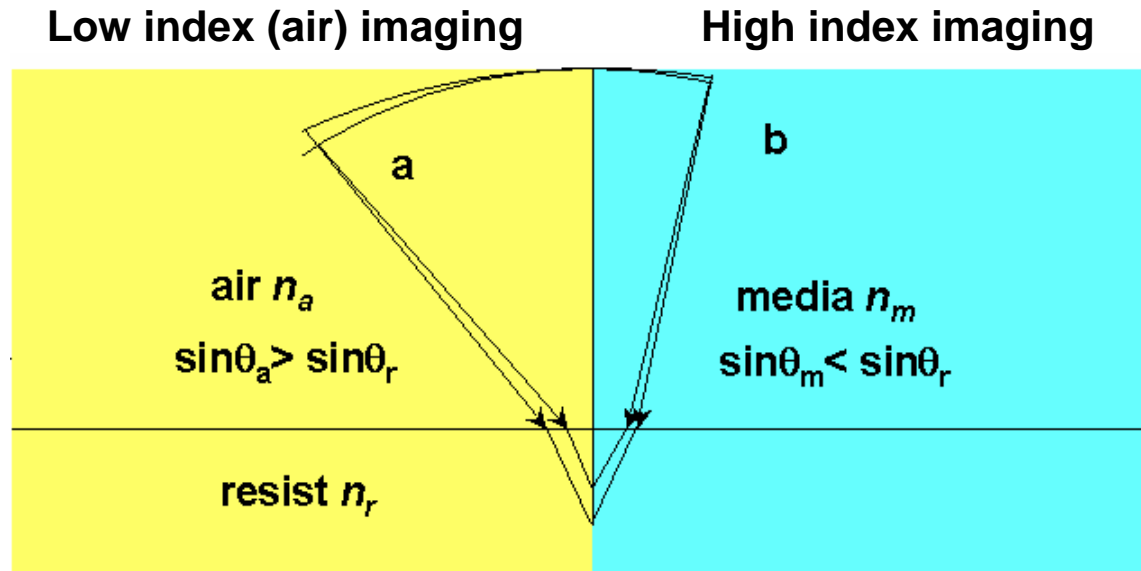
Binary mask 0.70σ
Unpolarized illumination
200-240nm pitch
TOK ISP topcoat
80nm TOK ILP03 resist
AR29 BARC

Remaining system action items:

Field stop and sigma apertures, environmental audit,
PSM, system qualification, polarization control

Homogeneous Immersion

Increasing refractive indices – the defocus effect



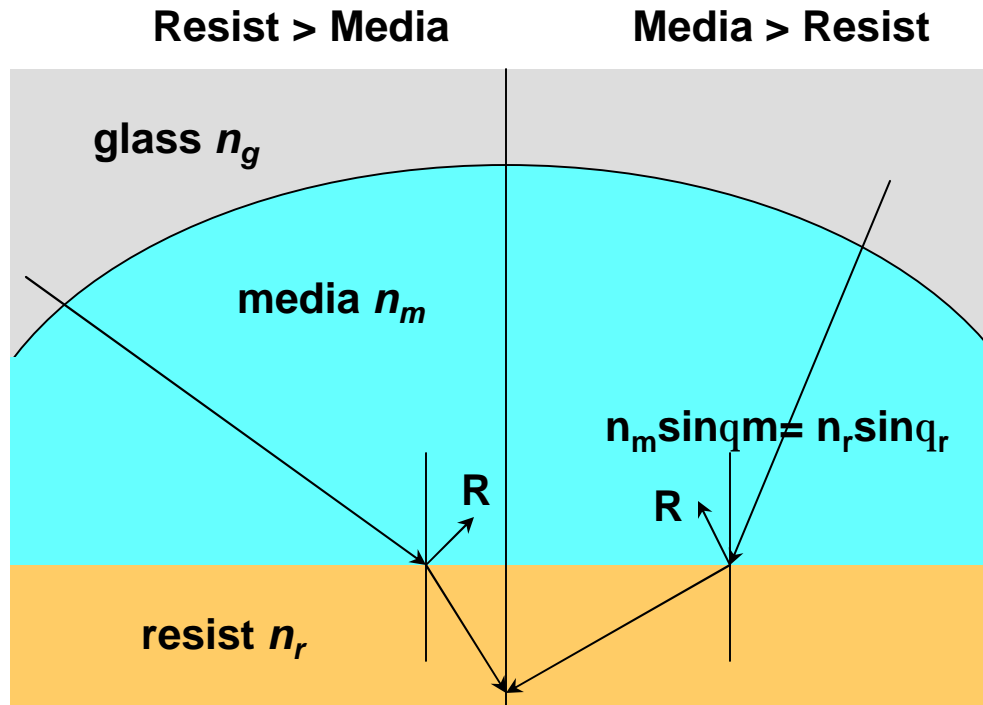
The defocus wave aberration is proportional to $\sin^2 q$

Higher indices reduce defocus OPD at equivalent NA values

Small NA/n is desirable

Homogeneous Immersion

Increasing refractive indices – the refractive effect



The glass index is not a concern unless surface is planar

The maximum NA is limited to $\min[n_m, n_r]$

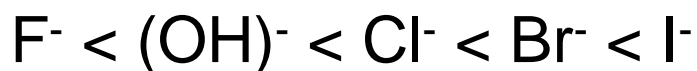
Reflectivity is determined by index disparity

Matched indices is desirable

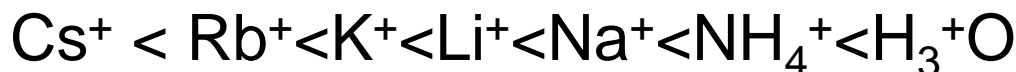
Increasing Water Index in the UV

Inorganic approach

- UV-vis absorption involves excitation of e^- from ground
- Solvents provide “charge-transfer-to-solvent” transitions (CTTS)
- CTTS and λ_{\max} for halide ions is well documented [1]



- Alkalai metal cations can shift λ_{\max} lower [2]



- $d\lambda_{\max}/dT$ is positive ($\sim 500\text{ppm}/^\circ\text{C}$), $d\lambda_{\max}/dP$ is negative
- Goal to approach “anomalous dispersion” with low absorbance

[1] E. Rabinowitch, *Rev. Mod. Phys.*, 14, 112 (1942)

[2] G. Stein and A. Treinen, *Trans. Faraday Soc.* 56, 1393 (1960)



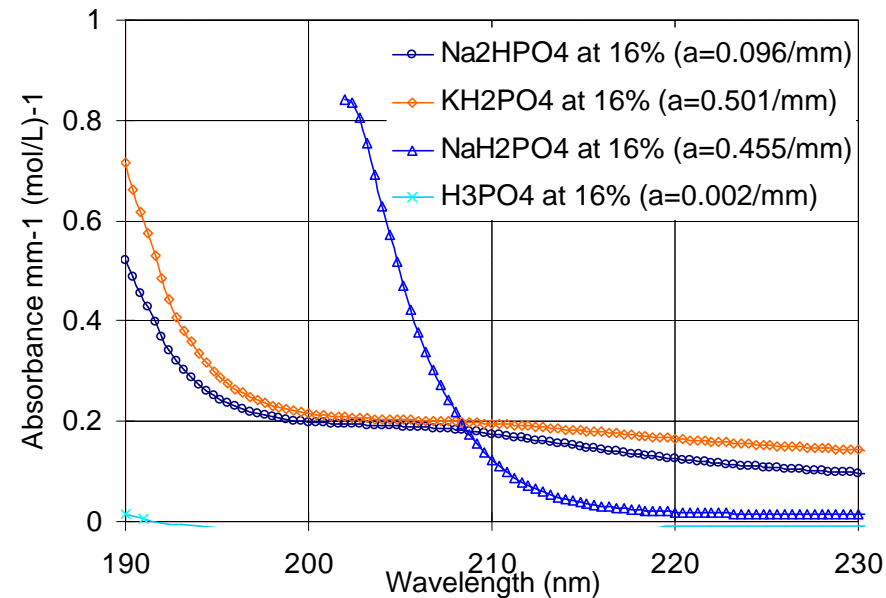
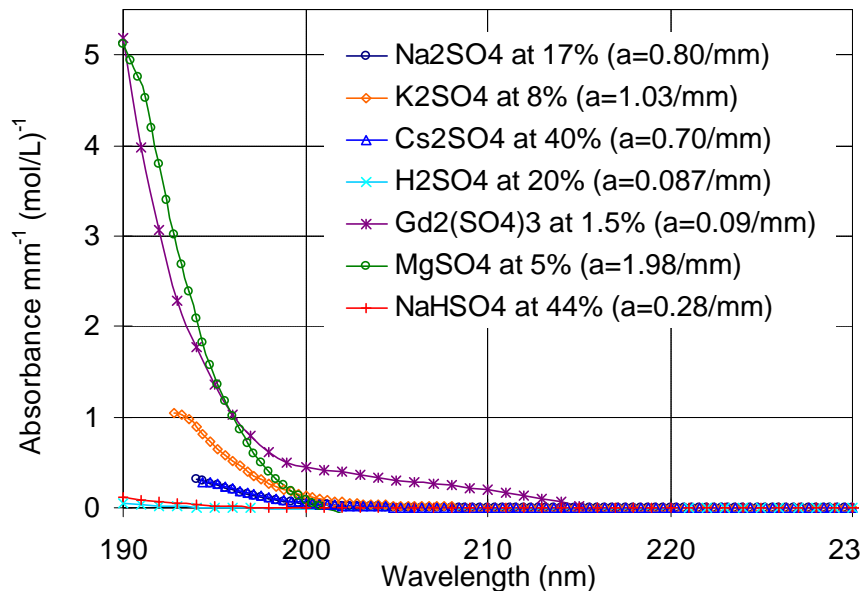
Effect of Anion on Absorption of Water

<i>Anion in water</i>	<i>Absorption Peak [3]</i>	
I ⁻	5.48eV	227nm
Br ⁻	6.26	198
<i>Cl⁻</i>	<i>6.78</i>	<i>183</i>
ClO ₄ ⁻¹	6.88	180
<i>HPO₄²⁻¹</i>	<i>6.95</i>	<i>179</i>
<i>SO₄²⁻¹</i>	<i>7.09</i>	<i>175</i>
<i>H₂PO₄⁻</i>	<i>7.31</i>	<i>170</i>
<i>HSO₄⁻</i>	<i>7.44</i>	<i>167</i>

[3] Various including M.J. Blandamer and M.F. Fox, Theory and Applications of Charge-Transfer-To-Solvent Spectra, (1968).

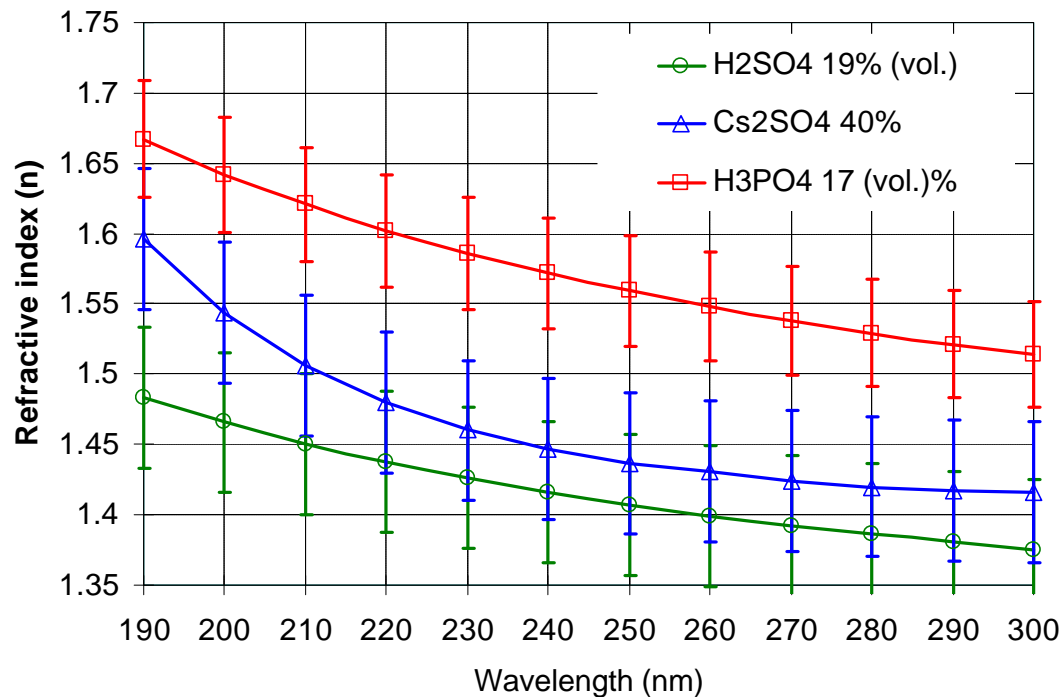


Measured Absorbance Spectra of Sulfates and Phosphates in Water



- Solutions normalized to mole concentration of cation
- Fluids with absorbance $< 0.1/\text{mm}$ become interesting
- Mixtures follow EMA behavior

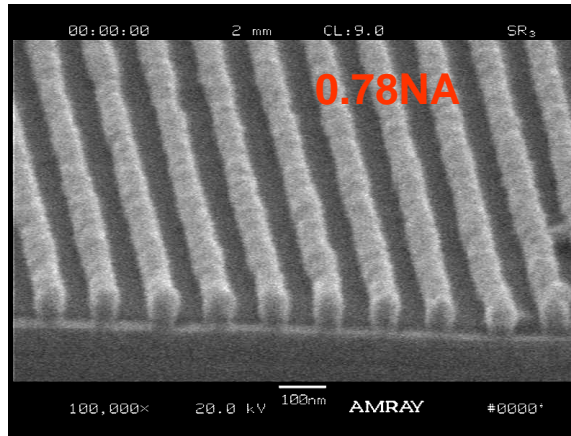
Measured Refractive Index of Select Sulfates and Phosphates in Water



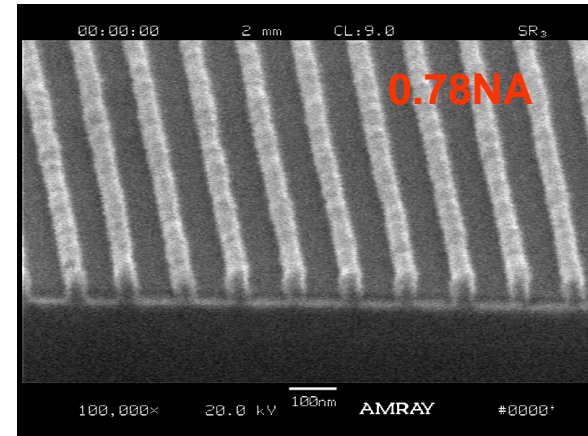
- Spectroscopic ellipsometry screening for Cauchy fit
- Several cations show little impact on index

Pure and Doped Water Comparisons for same angle (31°) in immersion fluids

Water with
40 wt%
 Cs_2SO_4
~100mm gap
117nm pitch

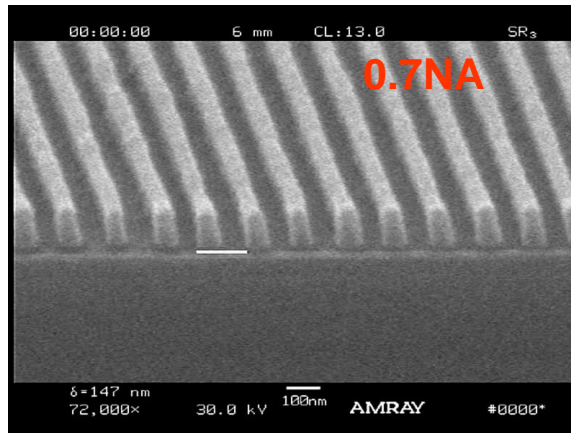


59nm 1:1 (50nm resist)

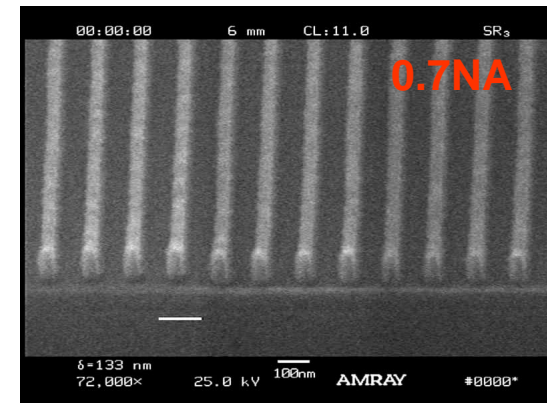


39nm 1:2 (50nm resist)

Water
(HPLC grade)
~100mm gap
130nm pitch



65nm 1:1 (100nm resist)

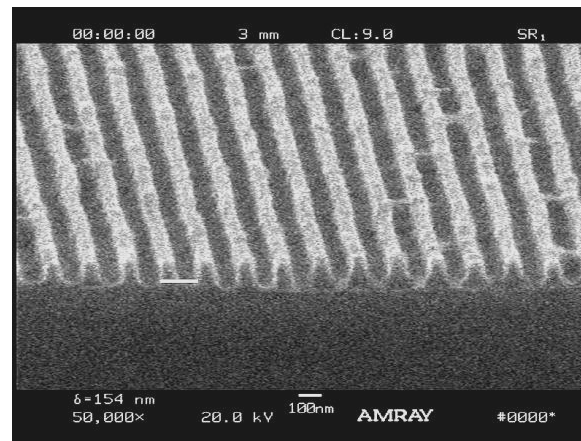


45nm 1:2 (70nm resist)

Summary

- 193nm immersion lithography to 38nm p/2
- Early optical results of water are promising for $n \sim 1.6$
- Resolution limit with 1.6n fluid is 30nm p/2

248nm Water Immersion Lithography



**75nm half-pitch
0.82NA**

Acknowledgements: DARPA / AFRL, International SEMATECH, SRC, IBM, Exitech, Corning Tropel, ASML, Intel, Shipley, TOK, Photonics, Brewer Science, GAM Laser Inc.